1. Record Nr. UNINA9910139771403321

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Titolo	Handbook of nitride semiconductors and devices . Vol. 2 Electronic and optical processes in nitrides [[electronic resource] /] / Hadis Morkoc
Pubbl/distr/stampa	Weinheim, : Wiley-VCH [Chichester, : John Wiley, distributor], c2008-c2009
ISBN	1-282-27952-1 9786612279522 3-527-62841-X 3-527-62842-8
Descrizione fisica	1 online resource (885 p.)
Collana	Handbook of Nitride Semiconductors and Devices (VCH)
Altri autori (Persone)	Morkoc Hadis
Disciplina	621.38152
Soggetti	Semiconductors - Materials Nitrides
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Handbook of Nitride Semiconductors and Devices; Contents; Preface; Color Tables; 1 Metal Contacts to GaN and Processing; Introduction; 1.1 A Primer for Semiconductor-Metal Contacts; 1.2 Current Flow in Metal-Semiconductor Junctions; 1.2.1 The Regime Dominated by Thermionic Emission; 1.2.2 Thermionic Field Emission Regime; 1.2.3 Direct Tunneling Regime; 1.2.4 Leakage Current; 1.3 GaN Schottky Barriers for High-Voltage Rectifiers; 1.4 Ohmic Contact Resistance; 1.4.1 Specific Contact Resistivity; 1.4.2 Semiconductor Resistance; 1.5 Determination of the Contact Resistivity 1.6 Ohmic Contacts to GaN1.6.1 Nonalloyed Ohmic Contacts; 1.6.2 Alloyed Ohmic Contacts on n-Type GaN; 1.6.3 Contacts to p-Type GaN and Transparent Conducting Oxides; 1.6.4 Effect of Surface Treatment on Ohmic Contacts; 1.6.5 Case of a Forward-Biased p-n Junction in Conjunction with Nonohmic Contacts to p-GaN; 1.7 Structural Analysis of Ohmic Contacts on GaN; 1.8 Etching Techniques for III Nitrides; 1.8.1 Dry (Plasma) Etching; 1.8.1.1 Electron Cyclotron Resonance Etching; 1.8.1.2 Ion Milling; 1.8.1.3 Reactive Ion Etching; 1.8.1.4 Inductively Coupled Plasma Etching

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Sommario/riassunto

The three volumes of this handbook treat the fundamentals, technology and nanotechnology of nitride semiconductors with an extraordinary clarity and depth. They present all the necessary basics of semiconductor and device physics and engineering together with an extensive reference section. Volume 2 addresses the electrical and optical properties of nitride materials. It includes semiconductor metal contacts, impurity and carrier concentrations, and carrier transport in semiconductors.